

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
IMEC312.001AUSAPPLICATION NO.
10/797888INFORMATION DISCLOSURE STATEMENT
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APPLICANT
Paraschiv, et al.FILING DATE
09-Mar-2004GROUP
1763

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
LV	1	2003-0104706-A1		Mitsubishi et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO

EXAMINER INITIAL		OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
LV	2	Barnett, et al.; Solid State Phenomena, Vol. 92, p. 11, 2003; "Wet Etch Enhancement of HfO ₂ Films by Implant Processing"
LV	3	Saenger, et al.; MRS Symposium Proceedings, Volume 745 (Novel Materials and Processes for advanced CMOS, Pennsylvania, p. 79 - 84, 2003; "A Selective Etching Process for Chemically Inert High-k Metal Oxides"
LV	4	Christenson, et al. Solid State Phenomena, Vol. 92, p. 129, 2003; "Selective Wet Etching of High-k Gate Dielectrics"

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060704

EXAMINER	DATE CONSIDERED
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